

CMNDM8001

SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



www.centrasemi.com

FEMTOmini™



SOT-953 CASE

• Device is *Halogen Free* by design

APPLICATIONS:

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

MAXIMUM RATINGS: (T_A=25°C)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Continuous Drain Current
Power Dissipation
Operating and Storage Junction Temperature

SYMBOL

V _{DS}	20
V _{GS}	10
I _D	100
I _D	200
P _D	250
T _J , T _{stg}	-65 to +150

UNITS

V
V
mA
mA
mW
°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

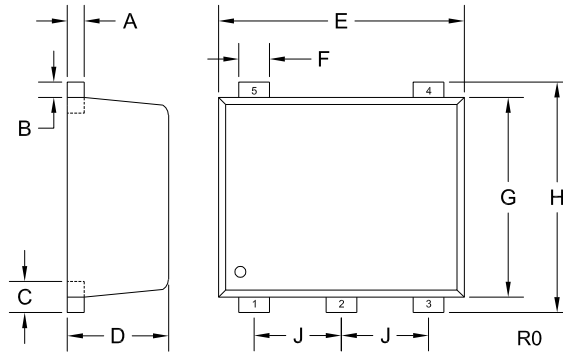
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{GSSF} , I _{GSSR}	V _{GS} =10V, V _{DS} =0			1.0	μA
I _{DSS}	V _{DS} =20V, V _{GS} =0			1.0	μA
BV _{DSS}	V _{GS} =0, I _D =100μA	20			V
V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.6		1.1	V
r _{DS(ON)}	V _{GS} =4.0V, I _D =10mA			8.0	Ω
r _{DS(ON)}	V _{GS} =2.5V, I _D =10mA			12	Ω
r _{DS(ON)}	V _{GS} =1.5V, I _D =1.0mA			45	Ω
g _{fs}	V _{DS} =10V, I _D =100mA	100			mS
C _{rss}	V _{DS} =3.0V, V _{GS} =0, f=1.0MHz		15		pF
C _{iss}	V _{DS} =3.0V, V _{GS} =0, f=1.0MHz		45		pF
C _{oss}	V _{DS} =3.0V, V _{GS} =0, f=1.0MHz		15		pF
t _{on}	V _{DD} =3.0V, V _{GS} =2.5V, I _D =10mA		35		ns
t _{off}	V _{DD} =3.0V, V _{GS} =2.5V, I _D =10mA		80		ns

R1 (25-January 2010)

CMNDM8001
SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



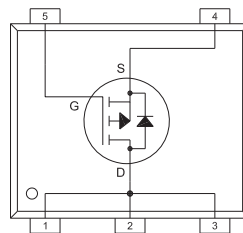
SOT-953 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.002	0.006	0.050	0.150
B	0.002	0.006	0.050	0.150
C	0.005	0.007	0.125	0.175
D	0.016	0.020	0.400	0.500
E	0.037	0.041	0.950	1.050
F	0.004	0.008	0.100	0.200
G	0.030	0.033	0.750	0.850
H	0.037	0.041	0.950	1.050
J	0.014		0.350	

SOT-953 (REV: R0)

PIN CONFIGURATION



LEAD CODE:

- 1) Drain
- 2) Drain
- 3) Drain
- 4) Source
- 5) Gate

MARKING CODE: BC

R1 (25-January 2010)

www.centalsemi.com

www.DataSheet4U.com